

PNP SILICON RF POWER TRANSISTOR

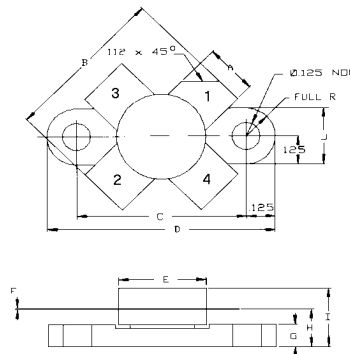
DESCRIPTION:

The **ASI 2N6097** is Designed for
12.5 V Large-Signal Amplifier
Applications to 175 MHz.

MAXIMUM RATINGS

I_C	6.0 A
V_{CEO}	18 V
V_{CB0}	36 V
P_{DISS}	60 W @ $T_J = 25^\circ\text{C}$
T_J	-65 to +200 $^\circ\text{C}$
T_{STG}	-65 to +150 $^\circ\text{C}$
θ_{JC}	2.9 $^\circ\text{C/W}$

PACKAGE STYLE .380" 4L FLG.



	MINIMUM Inches/mm	MAXIMUM Inches/mm
A	.220/5.59	.230/5.84
B	.785/19.94	
C	.720/18.29	.730/18.54
D	.970/24.64	.980/24.89
E		.385/9.78
F	.004/0.10	.006/0.15
G	.085/2.16	.105/2.67
H	.160/4.06	.180/4.57
I		.280/7.11
J	.240/6.10	.255/6.48

1 = COLLECTOR 2 = BASE
3 & 4 = EMITTER

CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 100\text{ mA}$	18			V
BV_{CES}	$I_C = 20\text{ mA}$	36			V
BV_{EBO}	$I_E = 10\text{ mA}$	4.0			V
I_{CBO}	$V_{CB} = 15\text{ V}$			2.5	mA
I_{CES}	$V_{CE} = 15\text{ V}$ $T_A = 55^\circ\text{C}$			10	mA
h_{FE}	$V_{CE} = 5.0\text{ V}$ $I_C = 500\text{ mA}$	5.0			---
C_{OB}	$V_{CB} = 12.5\text{ V}$ $f = 100\text{ KHz}$		310	400	pF
G_{PE}	$V_{CC} = 12.5\text{ V}$ $P_{OUT} = 40\text{ W}$ $f = 175\text{ MHz}$	4.5	5.0		dB
η_C	$V_{CC} = 12.5\text{ V}$ $P_{OUT} = 40\text{ W}$ $f = 175\text{ MHz}$	60			%

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REV. A

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